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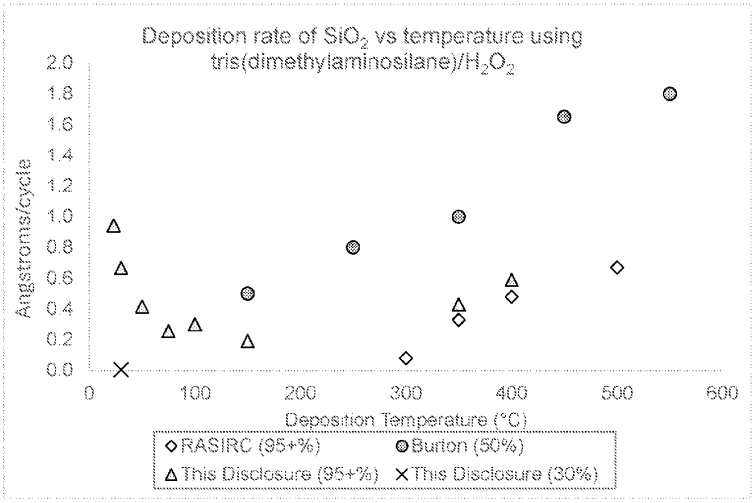
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(54) Title: LOW TEMPERATURE THERMAL DEPOSITION OF SILICON-CONTAINING FILMS USING LOW WATER CONTENT HYDROGEN PEROXIDE

Fig. 1



(57) Abstract: Provided are methods for low temperature thermal deposition of silicon-containing films. The methods provide selective deposition on a variety of substrates with high deposition rates and short cycle times.

[Continued on next page]

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